

DESCRIPTION

The SI2302A uses advanced trench technology to provide excellent $R_{DS(on)}$. This device is suitable for use as a uni-directional or bi-directional load switch.

V_{DSS} 20 V
 I_D 6 A
 $R_{DS(on)}$ 20 m Ω

FEATURES

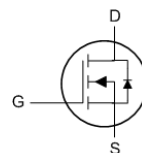
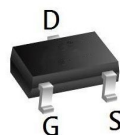
N-Channel Enhancement Mode Field Effect Transistor

- $V_{DSS} = 20\text{ V}$ $I_D = 6.0\text{ A}$
- $R_{DS(on)} < 30\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- $R_{DS(on)} < 40\text{ m}\Omega @ V_{GS} = 2.5\text{ V}$
- $R_{DS(on)} < 73\text{ m}\Omega @ V_{GS} = 1.8\text{ V}$

A2SHB

SOT23-3L top view

Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	6	A
Pulsed Drain Current	I_{DM}	25	
Maximum Body-Diode Continuous Current	I_S	2	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

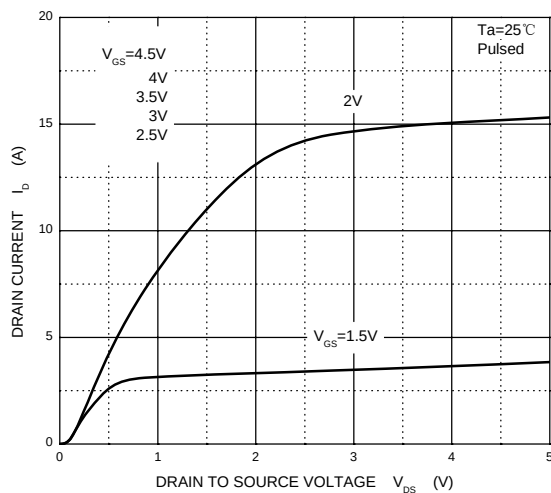
Electrical characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate-source leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			1.0	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.7	1.0	V
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 5.0A$		20	30	m Ω
		$V_{GS} = 2.5V, I_D = 4.0A$		26	40	
		$V_{GS} = 1.8V, I_D = 2.0A$			73	
Diode forward voltage	V_{SD}	$V_{GS} = 0V, I_S = 1A$		0.75	1	V
Forward transconductance	g_{fs}	$V_{DS} = 5V, I_D = 3.8A$	4			S
DYNAMIC PARAMETERS*						
Input capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		630		pF
Output capacitance	C_{oss}			164		
Reverse transfer capacitance	C_{rss}			137		
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.5		Ω
SWITCHING PARAMETERS*						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 5V, V_{DS} = 10V,$ $R_L = 1.7\Omega, R_{GEN} = 6\Omega$		5.5		ns
Rise time	t_r			14		
Turn-off delay time	$t_{d(off)}$			29		
Fall time	t_f			10.2		

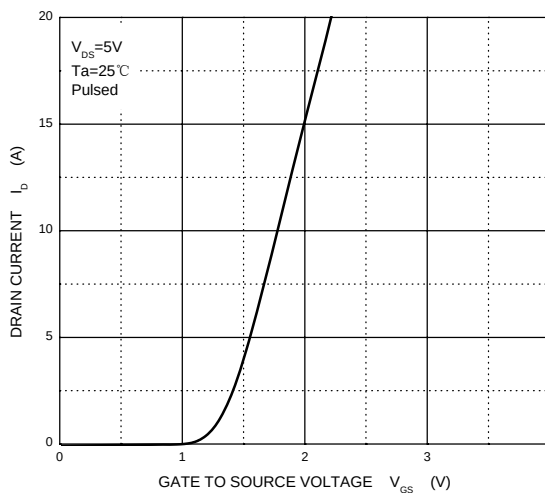
*These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES

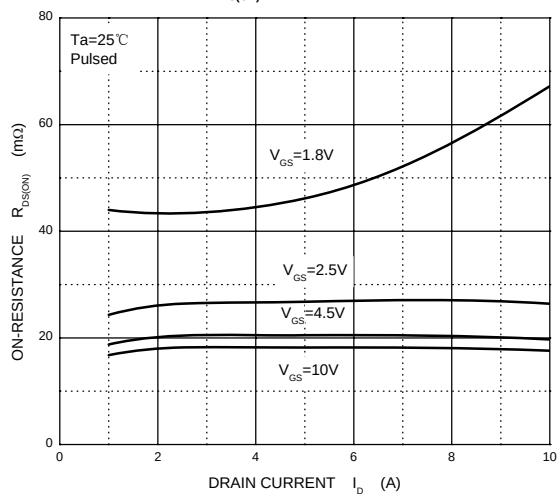
Output Characteristics



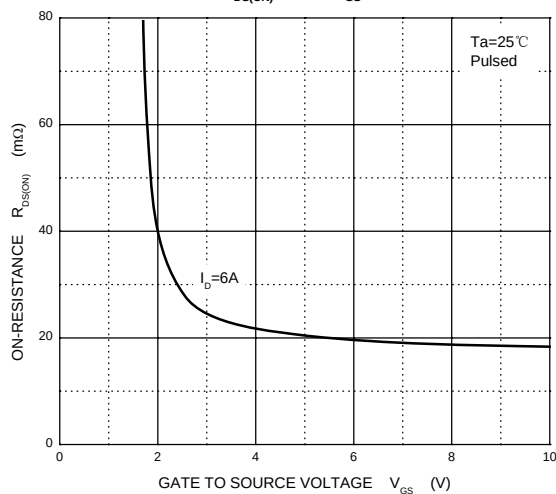
Transfer Characteristics



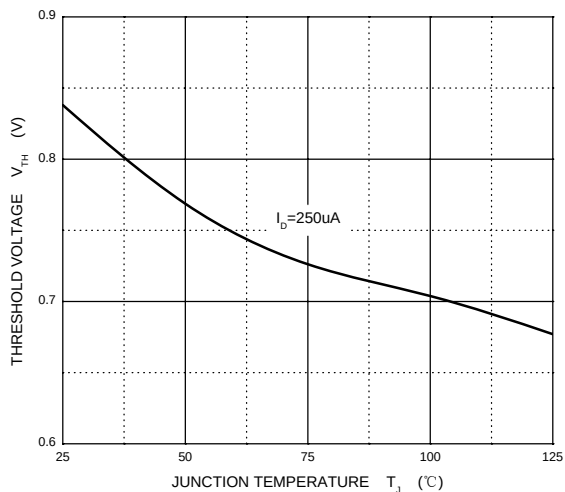
$R_{DS(ON)}$ — I_D



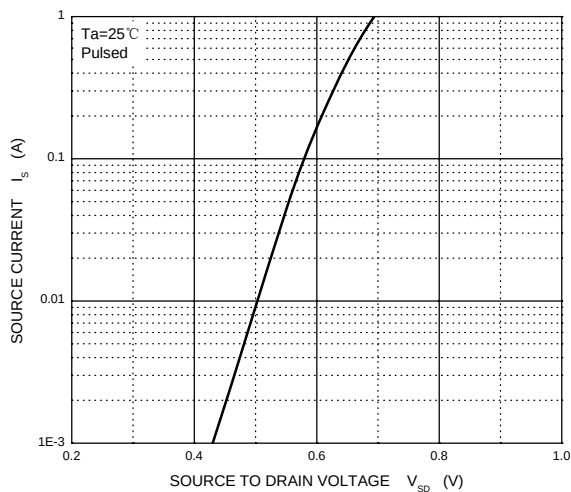
$R_{DS(ON)}$ — V_{GS}



Threshold Voltage

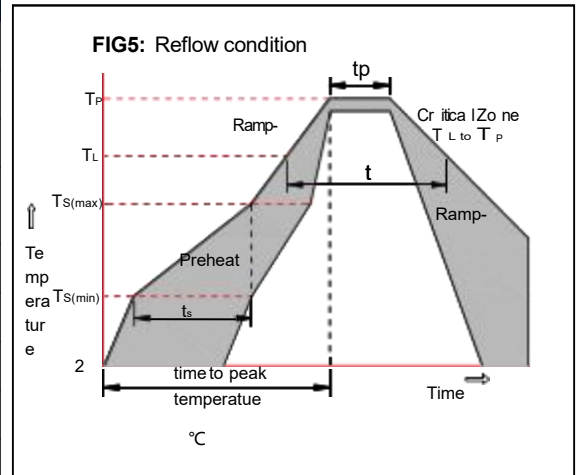


I_S — V_{SD}



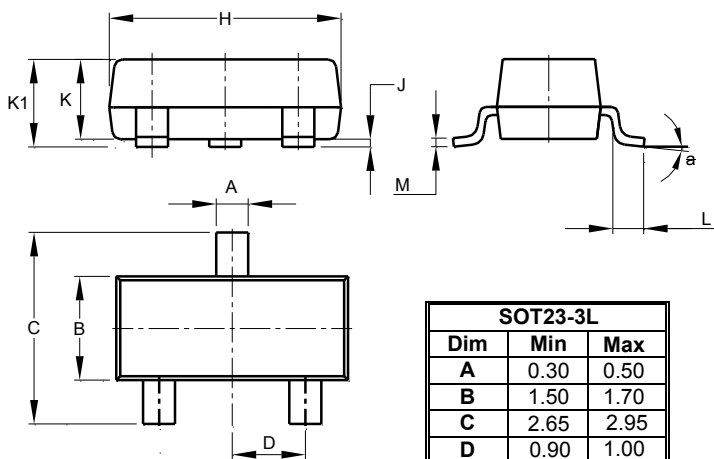
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

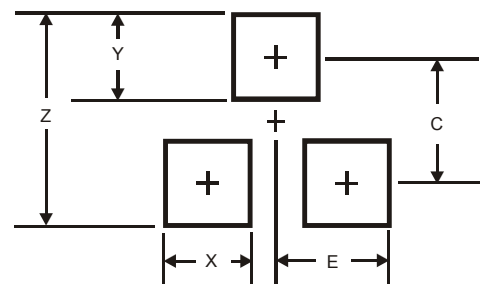


Package Dimensions & Suggested Pad Layout

SOT23-3L



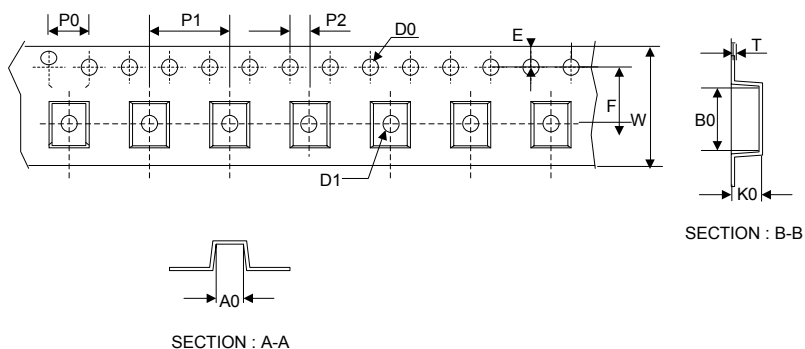
SOT23-3L		
Dim	Min	Max
A	0.30	0.50
B	1.50	1.70
C	2.65	2.95
D	0.90	1.00
H	2.82	3.02
J		0.10
K	1.05	1.15
K1	1.05	1.25
L	0.30	0.60
M	0.10	0.20
a	0°	8°
All Dimensions in mm		



Dimensions	SOT23-3L
Z	3.3
X	0.9
Y	1.0
C	2.3
E	1.40

Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.05±0.20
E	1.55±0.20
F	3.60±0.20
W	8.00±0.20
A0	3.80±0.20
B0	3.50±0.20
K0	1.55±0.20
T	0.25±0.15
D2	178.0±5.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0

Quantity: 3000PCS

7" Reel

